

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Canceled)
2. (Currently Amended) A method for forming ~~an insulating~~ a ceramic film comprising the steps of:
 - introducing a reactive gas into a reaction chamber;
 - applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;
 - applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and
 - forming the ~~insulating ceramic~~ film on a surface of an object in said reaction chamber, wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave,
 - wherein said reactive gas is introduced into said reaction chamber in a direction toward the surface of the object.
3. (Previously Presented) A method according to claim 2 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.
4. (Currently Amended) A method for forming ~~an insulating ceramic~~ a film comprising the steps of:
 - introducing a reactive gas into a reaction chamber;
 - applying a pulsed microwave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed microwave; and

forming the ~~insulating ceramic~~ film on a surface of an object in the reaction chamber using the plasma,

wherein a power value of said pulsed microwave is higher than a power value of said continuous electromagnetic wave,

wherein said reactive gas is introduced into said reaction chamber in a direction toward the surface of the object.

5. (Previously Presented) A method according to claim 4 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

6. (Currently Amended) A method for forming ~~an insulating ceramic~~ a film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the ~~insulating ceramic~~ film on a surface of an object in said reaction chamber,

wherein said reactive gas is introduced into said reaction chamber in a direction toward the surface of the object,

wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave, and

wherein a frequency of said pulsed electromagnetic wave is the same as a frequency of said continuous electromagnetic wave.

7. (Previously Presented) A method according to claim 6 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

8. (Currently Amended) A method for forming ~~an insulating ceramic~~ a film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the ~~insulating ceramic~~ film on a surface of an object in said reaction chamber, wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave,

wherein a frequency of said pulsed electromagnetic wave is different from a frequency of said continuous electromagnetic wave, and

wherein said reactive gas is introduced into said reaction chamber in a direction toward the surface of the object.

9. (Previously Presented) A method according to claim 8 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

10. (Currently Amended) A method for forming a metallic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and

forming the metallic film on a surface of an object in said reaction chamber,

wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave, and

wherein said reactive gas is introduced into said reaction chamber in a direction toward the surface of the object.

11. (Previously Presented) A method according to claim 10 wherein said metallic film comprises a material selected from the group consisting of tungsten, titanium, molybdenum and a silicide thereof.

12. (Previously Presented) A method according to claim 10 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

13. (Currently Amended) A method for forming a metallic film comprising the steps of:

introducing a reactive gas into a reaction chamber;

applying a pulsed microwave to said reactive gas to convert said reactive gas into a plasma;

applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed microwave; and

forming the metallic film on a surface of an object in the reaction chamber using the plasma,

wherein a power value of said pulsed microwave is higher than a power value of said continuous electromagnetic wave,

wherein said reactive gas is introduced into said reaction chamber in a direction toward the surface of the object.

14. (Previously Presented) A method according to claim 13 wherein said metallic film comprises a material selected from the group consisting of tungsten, titanium, molybdenum and a silicide thereof.

15. (Previously Presented) A method according to claim 13 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

16. (Currently Amended) A method for forming a metallic film comprising the steps of:

introducing a reactive gas into a reaction chamber;
applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;
applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and
forming the metallic film on a surface of an object in said reaction chamber,
wherein said reactive gas is introduced into said reaction chamber in a direction toward the surface of the object,
wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave, and
wherein a frequency of said pulsed electromagnetic wave is the same as a frequency of said continuous electromagnetic wave.

17. (Currently Amended) A method according to claim ~~[[18]]~~ 16 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

18. (Currently Amended) A method for forming a metallic film comprising the steps of:
introducing a reactive gas into a reaction chamber;
applying a pulsed electromagnetic wave to said reactive gas to convert said reactive gas into a plasma;
applying a continuous electromagnetic wave to said reactive gas so that said continuous electromagnetic wave is superposed on said pulsed electromagnetic wave; and
forming the metallic film on a surface of an object in said reaction chamber,
wherein a power value of said pulsed electromagnetic wave is higher than a power value of said continuous electromagnetic wave,
wherein a frequency of said pulsed electromagnetic wave is different from a frequency of said continuous electromagnetic wave, and
wherein said reactive gas is introduced into said reaction chamber in a direction toward the surface of the object.

19. (Previously Presented) A method according to claim 18 wherein said metallic film comprises a material selected from the group consisting of tungsten, titanium, molybdenum and a silicide thereof.

20. (Previously Presented) A method according to claim 18 further comprising a step of applying a magnetic field for performing an electron cyclotron resonance in said reaction chamber.

21. (New) A method according to claim 2 wherein said film comprises a material selected from the group consisting of carbon, diamond like carbon, i-carbon, metal, and insulating ceramics.

22. (New) A method according to claim 4 wherein said film comprises a material selected from the group consisting of carbon, diamond like carbon, i-carbon, metal, and insulating ceramics.

23. (New) A method according to claim 6 wherein said film comprises a material selected from the group consisting of carbon, diamond like carbon, i-carbon, metal, and insulating ceramics.

24. (New) A method according to claim 8 wherein said film comprises a material selected from the group consisting of carbon, diamond like carbon, i-carbon, metal, and insulating ceramics.